

PSMN3R0-30YLD

N-channel 30 V, 3.0 m Ω logic level MOSFET in LFPAK56 using NextPowerS3 Technology

18 February 2014

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G, Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, gualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	91	W



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tj	junction temperature		-55	-	175	°C
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	3.2	4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	2.57	3.1	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13	-	4.5	6.7	nC
Q _{G(tot)}	total gate charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13	-	14.5	21.9	nC
Source-drain	diode					,
S	softness factor	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{DS} = 15 \text{ V}; Fig. 16$	-	1.07	-	

^[1] Continuous current is limited by package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source	[d	G F
4	G	gate	فققف	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PSMN3R0-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R0-30YLD	3D030L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	91	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	90	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	512	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	НВМ		500	-	V
Source-drain	n diode			'		
Is	source current	T _{mb} = 25 °C		-	76	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	512	Α
Avalanche r	uggedness	1	1	-		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 25 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; t_p = 467 μs	[2]	-	227.5	mJ

^[1] Continuous current is limited by package.

^[2] Protected by 100% test

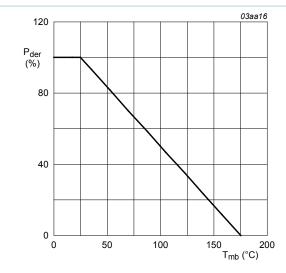
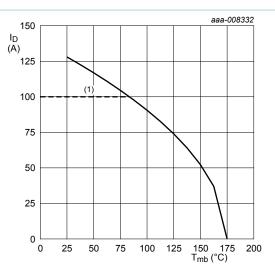


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

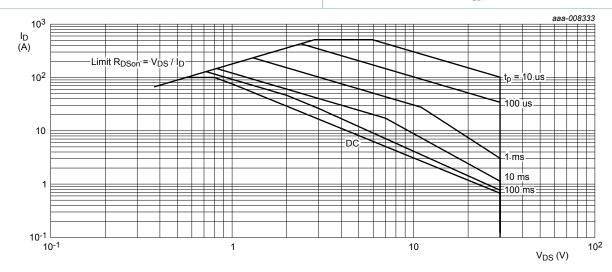


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	1.46	1.64	K/W

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	Fig. 5	-	50	-	K/W
	from junction to ambient	Fig. 6	-	125	-	K/W

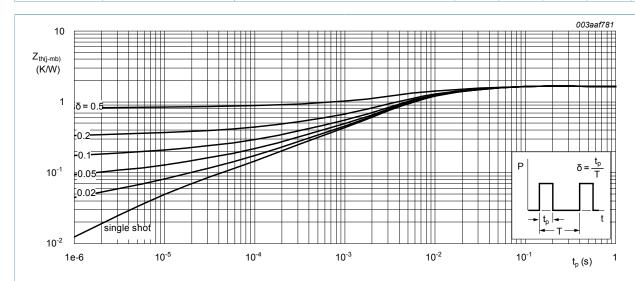


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

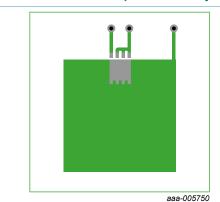


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

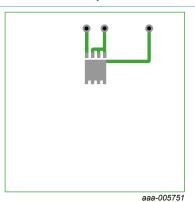


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. Characteristics

Table 1. Cit	aracteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charact	eristics					
V _{(BR)DSS}	•	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C < T _j < 150 °C	-	-4.3	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 24 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 24 V; V _{GS} = 0 V; T _j = 125 °C	-	0.82	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10	-	3.2	4	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	6.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	2.57	3.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	5.1	mΩ
R _G	gate resistance	f = 1 MHz	-	0.57	1.14	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	31	46.4	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	14.5	21.9	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	28.5	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	4.9	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	2.9	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	2	-	nC
Q_{GD}	gate-drain charge		-	4.5	6.7	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.75	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	1959	2939	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	1029	1543	pF
C _{rss}	reverse transfer capacitance		-	140	210	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω ; V_{GS} = 4.5 V;	-	13.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	21	-	ns
t _{d(off)}	turn-off delay time	-	-	16.9	-	ns
t _f	fall time		-	12.4	-	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	21.8	-	nC
Source-dra	in diode			'			
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	29.2	58.3	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	19	38.1	nC
t _a	reverse recovery rise time			-	14.1	-	ns
t _b	reverse recovery fall time			-	15.1	-	ns
S	softness factor			-	1.07	-	

[1] includes capacitive recovery

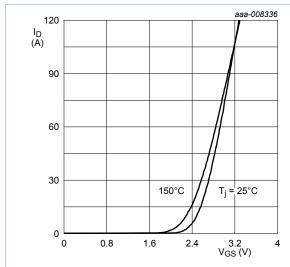
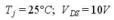


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values



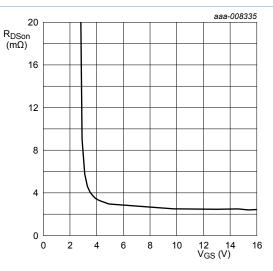


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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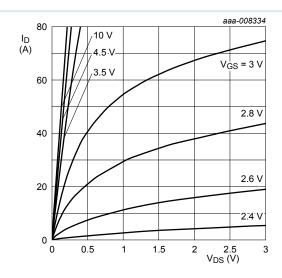


Fig. 9. Output characteristics; drain current as a function of drain-source voltage; typical values

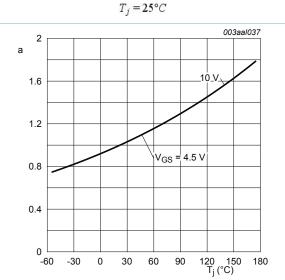


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

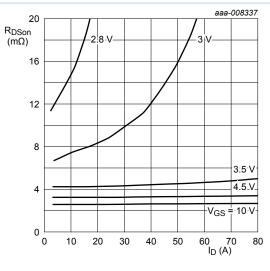


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

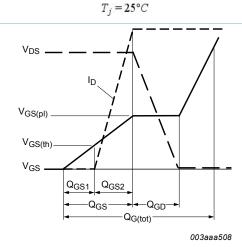


Fig. 12. Gate charge waveform definitions

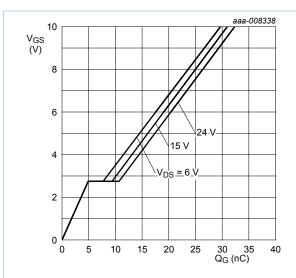


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

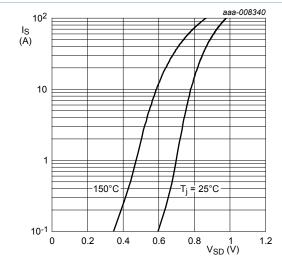


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

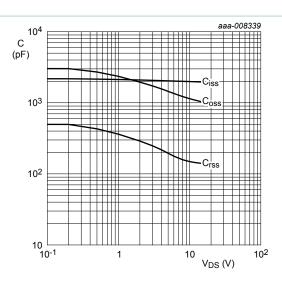


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

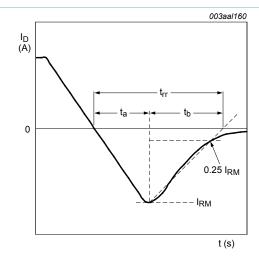
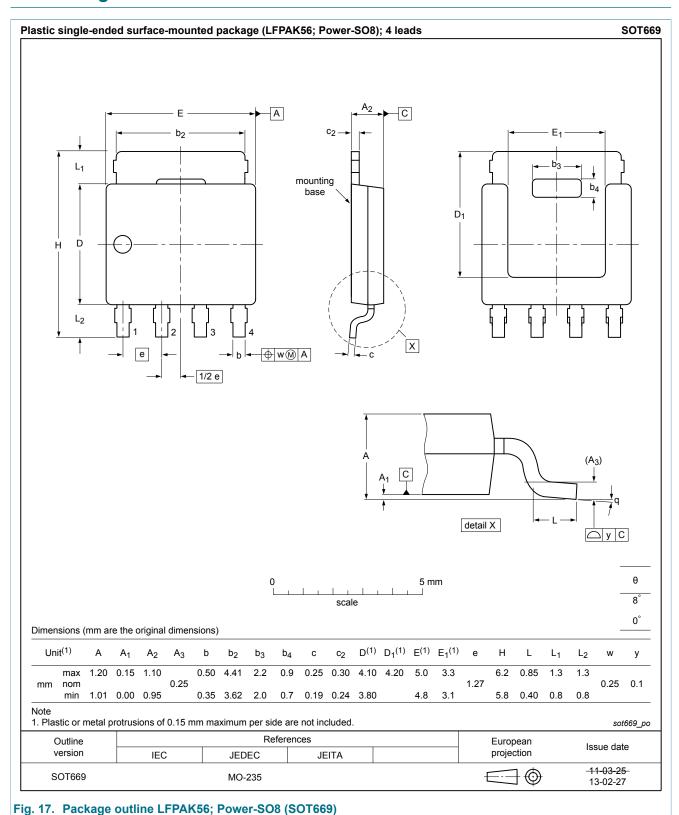


Fig. 16. Reverse recovery timing definition

11. Package outline



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